X-Ray Diffraction


| Peak | InGaN QW | GaN | AlGaN barrier | AlGaN |
| :--- | :---: | :---: | :---: | :---: |
| Diffraction Angle | $17.285^{\circ}$ |  |  |  |
| Intensity | $1375,0^{\prime}$ |  |  |  |
| FWHM | $252^{\prime \prime}$ |  |  |  |


|  | InGaN QW |
| :--- | :---: |
| In content | - |
| QW thickness | - |
| barrier thickness | - |



Confidential

I-V Characteristics


P-GaN Electrical Properties (TLM)

Sheet Resistance $\quad$ Rs $=24351 \Omega /$

Contact Resistance $\quad \mathrm{Rc}=3 \mathrm{E}-03 \quad \Omega . \mathrm{cm}^{2}$
P-GaN resistivity $\rho=0.37 \Omega . \mathrm{cm}$

